

MOS INTEGRATED CIRCUIT

 μ PD16858B/C

THREE-PHASE SPINDLE MOTOR DRIVER FOR MONOLITHIC CD-ROM

DESCRIPTION

The μ PD16858B/C is a three-phase spindle motor driver for CD-ROM drives and consists of a CMOS control circuit and a MOS bridge output.

This motor driver employs a three-phase full-wave PWM driving method. Because it has an output stage consisting of MOS FETs, the motor driver consumes less power than the existing linear drivers using bipolar transistors.

The product is supplied in the form of a small, slim 30-pin shrink SOP.

This spindle motor driver is ideal for driving slim-type spindle motors in notebook PCs and so on.

FEATURES

- Both normal PWM type (16858B) and synchronous rectification PWM type (16858C) are available.
- Low ON resistance (sum of ON resistances of upper and lower MOS FETs): Ron = 0.8Ω (TYP)
- · Low power consumption to three-phase full-wave PWM driving
- START/STOP pin is provided. Brake is applied in STOP mode.
- · Standby pin is provided. Internal circuitry is turned off in standby mode.
- Low current consumption: IDD = 3 mA (MAX), IDD (ST) = 1 μ A (MAX), torque command current = 30 μ A (MAX)
- · Thermal shut-down circuit and current-limiting circuit
- · Low-voltage malfunctioning prevention circuit
- · FG output function
- · Reverse rotation prevention circuit
- Hole bias function
- 30-pin shrink SOP (300 mil)

ORDERING INFORMATION

Part Number	Package
μPD16858BGS-GJG	30-pin shrink SOP (0.65-mm pitch, 300 mil)
μPD16858CGS-GJG	30-pin shrink SOP (0.65-mm pitch, 300 mil)

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ABSOLUTE MAXIMUM RATINGS

(T_A = 25 °C, 1 Ω /1 mH load condition: mounted on glass epoxy substrate measuring 100 mm \times 100 mm \times 1 mm with 15% of copper foil)

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	V _{DD}		-0.5 to +5.7	V
	Vм		-0.5 to +5.7	V
Input voltage	Vin		-0.5 to V _{DD} + 0.5	V
Steady-state DC output currentNote 1	ID (DC)	DC	±0.5	A/phase
Steady-state instantaneous output currentNote 2	D (pulse)	PW ≤ 5 ms, Duty ≤ 30 %	±1.3	A/phase
Output current at reverse brakeNote 3	IDR (pulse)	PW ≤ 5 ms, Duty ≤ 30 %	±1.5	A/phase
Power consumption	Рт		1.0	W
Peak joint temperature	Tch (MAX)		150	°C
Storage temperature range	T _{stg}		-55 to +150	°C

Notes 1. Rated current at constant-speed revolution

- 2. Rated current on starting or locking
- 3. Rated current at reverse brake

RECOMMENDED OPERATING CONDITIONS

(T_A = 25 °C, 1 Ω /1 mH load condition: mounted on glass epoxy substrate measuring 100 mm \times 100 mm \times 1 mm with 15% of copper foil)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply voltage	V _{DD}	4.5		5.5	V
	Vм	4.5		5.5	V
Steady-state DC output currentNote 1	I _D (DC)			±0.4	A/phase
Steady-state instantaneous output currentNote 2	ID (pulse)			±1.0	A/phase
Output current at reverse brakeNote 3	IDR (pulse)			±1.2	A/phase
Hole bias current	Інв		10	20	mA
IND pin output current	lfG	0	±2.5	±5	mA
Operating temperature range	TA	-20		75	°C

Notes 1. Recommended maximum current at constant-speed revolution

- 2. Recommended maximum current on starting or locking (It is recommended that the current be limited to 1.0 A or less.)
- 3. Recommended maximum current at reverse brake





ELECTRICAL SPECIFICATIONS (Unless otherwise specified, $T_A = 25$ °C, $V_{DD} = V_M = 5$ V)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
[Overall]						
Current consumption 1 (during operation)	IDD	STB = VDD			3.0	mA
Current consumption (in standby mode)	IDD (ST)	STB = GND			1.0	μΑ
[ST/SP, STB, REV]						
High-level input voltage	VIH		0.6 V _{DD}		V _{DD}	V
Low-level input voltage	VIL				0.8	V
Input pull-down resistor	RIND			120		kΩ
[Control circuit]						
Triangular wave oscillation frequency	fрwм	C _T = 100 pF		75		kHz
[Hole amplifier]						
In-phase input voltage range	V _{Hch}		1.5		3.5	V
Hysteresis voltage	V _{Hhis}	V _H = 2.5 V		15		mV
Input bias current	Hbias				1.0	μΑ
[Hole bias block]						
Hole bias voltage	Vнв	Iнв = 10 mA		0.3	0.5	V
[FG output]						
IND pin high-level voltage	V _{FG_H}	IFG = -2.5 mA	V _{DD} -1.0			V
IND pin low-level voltage	V _{FG_L}	IFG = +2.5 mA			0.5	V
[Output block]						
Output ON resistance (upper + lower)	Ron	$I_{DR} = 200 \text{ mA}$ $T_{A} = -20 \text{ to } +75 ^{\circ}\text{C}$		0.8	1.2	Ω
OFF leakage current	I _D (OFF)				10	μΑ
Output turn-on time	tonh	R _M = 5 Ω			1.0	μs
Output turn-off time	tоffн	Star wiring			1.0	μs
[Torque command]						
Control reference input voltage range	ECR		0.3		4.0	V
Control input voltage range	EC		0.3		4.0	V
Input current	lin	EC, ECR = 0.5 to 3 V			30	μΑ
Input voltage difference	ECR-ECNote	DUTY = 100 %, ECR = 2.0 V		1.1		V
DEAD ZONE (+)	EC_d+	ECR = 2.0 V	0		100	mV
DEAD ZONE (-)	EC_d-	ECR = 2.0 V	0		-100	mV
[Overcurrent detector]						
Input offset voltage	Vio		-15		+15	mV

Note Excluding the dead zone.

The overheating protection circuit (T.S.D) operates at $T_{CH} > 150 \, ^{\circ}C$.

The low-voltage malfunctioning prevention circuit (UVLO) operates at 4 V (TYP).





PIN FUNCTION

Package: 30-pin shrink SOP (300 mil)

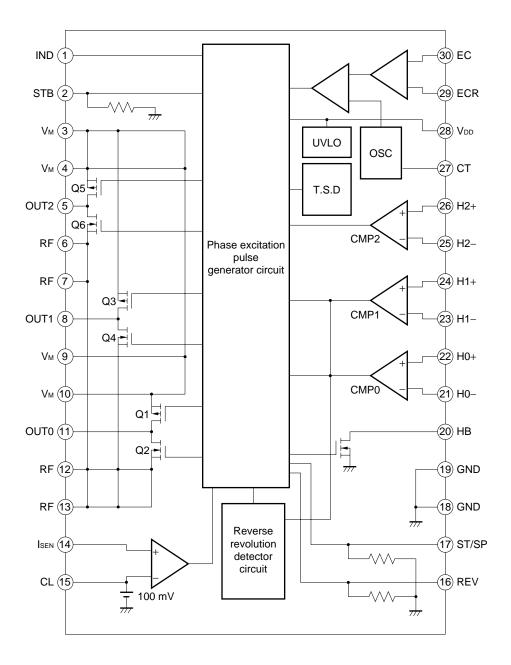
IND □	1 O	30	⊟ EC
STB 🗀	' •		ECR
	2	29	
Vм 🗀	3	28	□ Vdd
Vм 🗀	4	27	□ст
OUT2 🗀	5	26	□ H2+
RF □	6	25	□ H2–
RF □	7	24	□ H1+
OUT1 🗖	8	23	□ H1-
Vм 🗀	9	22	□ H0+
Vм 🗀	10	21	□ H0−
OUT0 🗖	11	20	⊐ НВ
RF □	12	19	□ GND
RF □	13	18	□ GND
ISEN 🗀	14	17	□ ST/SP
CL 🗀	15	16	□ REV
			ı

Pin No	Pin Name	Pin Function
1	IND	Index signal output pin
2	STB	Standby operation input pin
3	VM	Motor block supply voltage input pin
4	Vм	Motor block supply voltage input pin
5	OUT2	Motor connection pin
6	RF	Three-phase bridge common pin
7	RF	Three-phase bridge common pin
8	OUT1	Motor connection pin
9	VM	Motor block supply voltage input pin
10	Vм	Motor block supply voltage input pin
11	OUT0	Motor connection pin
12	RF	Three-phase bridge common pin
13	RF	Three-phase bridge common pin
14	Isen	Sense resistor connection pin
15	CL	Overcurrent detection voltage filter pin
16	REV	Reverse operation input pin
17	ST/SP	Start/stop input pin
18	GND	GND pin
19	GND	GND pin
20	НВ	Hole bias pin
21	H0-	Hole signal input pin
22	H0+	Hole signal input pin
23	H1-	Hole signal input pin
24	H1+	Hole signal input pin
25	H2-	Hole signal input pin
26	H2+	Hole signal input pin
27	Ст	Oscillation frequency setting capacitor connection pin
28	V _{DD}	Control system supply voltage input pin
29	ECR	Control reference voltage input pin
30	EC	Control voltage input pin
D 1		and the second of the second o

Remark Where more than one pin with the same name exists (such as V_M , RF, and GND), connect all of them, not just one of them.



BLOCK DIAGRAM

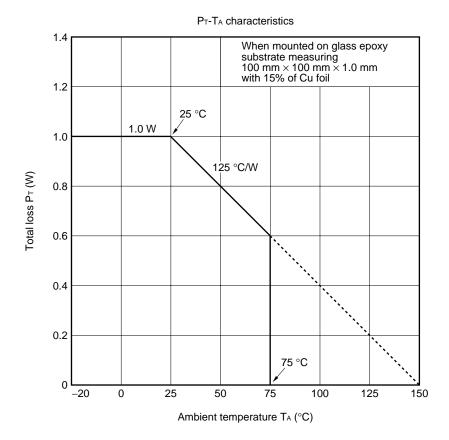


Remarks 1. The CL pin is used to connect a filter. Leave this pin open when it is not used.

2. Where more than one pin with the same name exists (such as V_M, RF, and GND), connect all of them, not just one of them.



TOTAL LOSS VS AMBIENT TEMPERATURE CHARACTERISTICS



Caution If the ambient temperature is 25 °C or less, a power of up to 1 W can be applied. If the temperature rises beyond 25 °C, perform derating by referring to the above figure. At 75 °C, which is the maximum level of the recommended operating temperature, a power of up to 0.6 W can be applied to the IC.





FUNCTION OPERATION TABLE

(1) ST/SP = "H"

	Input	Signal		Circuit Operation Mode	$Source \to Sink$
CMP0	CMP1	CMP2	PWM		
Н	Н	L	Н	Operate	$W\toV$
Н	Н	L	L	Brake	
Н	L	L	Н	Operate	$W\toU$
Н	L	L	L	Brake	
Н	L	Н	Н	Operate	$V\toU$
Н	L	Н	L	Brake	
L	L	Н	Н	Operate	$V\toW$
L	L	Н	L	Brake	
L	Н	Н	Н	Operate	$U\toW$
L	Н	Н	L	Brake	
L	Н	L	Н	Operate	$U \to V$
L	Н	L	L	Brake	

Brake: Regenerated via parasitic diode of high-side Pch MOS FET (μ PD16858B). Regenerated via high-side Pch MOS FET channel (μ PD16858C).

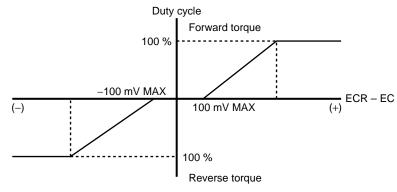
(2) ST/SP = "L"

	Input	Circuit Operation Mode		
CMP0	CMP1	CMP2	PWM	
_	-	-	_	Short brake

Short brake: High-side MOS FET turns ON and low-side MOS FET turns OFF.

(3) Torque command

The relation between the difference between the control reference voltage (ECR) and control voltage (EC) (ECR – EC) and torque is as follows:



	Reverse Pin \	/oltage (REV)
	L	Н
ECR > EC	Forward	Reverse ^{Note}
ECR < EC	Reverse ^{Note}	Stop

Note Stops if reverse revolution is detected.

During reverse revolution, the counter electromotive current flows through the parasitic diode of the Pch MOS FET at the high side (μ PD16858B), or the channel of Pch MOS FET at the high side (μ PD16858C).



(4) Standby mode

The power supplied to the internal circuitry of the IC can be turned off by setting the IC in the standby mode. In the standby mode, each pin goes into a high-impedance state (H bridge all OFF). The internal oscillation block also stops and therefore, the circuit current can be decreased.

If the motor driver is stopped by using the standby pin while the driver is operating, the motor is stopped by force of inertia. It takes the motor driver about several 10 μ s to start when it is set in the normal operation mode.

STB Pin	Operation Mode
Н	Normal mode
L	Standby mode

Caution Output current

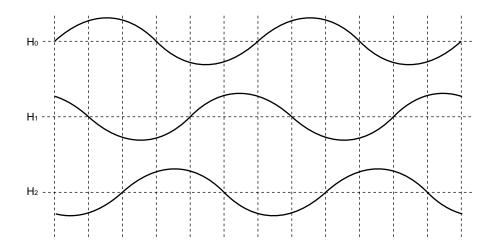
The rated output current differs depending on whether the motor revolves at a constant speed (steady state), is started (steady state), or reversed and brake is applied. The rated DC current when the motor revolves at a constant speed is 0.5 A, and the rated instantaneous current when the motor is started is 1.3 A. When brake is applied to stop the motor and when the motor is reversed, the maximum current is 1.5 A.

When a brake is applied or the motor is reversed, a current exceeding that when the motor revolves at a constant speed (immediately before a brake is applied) instantaneously flows because of the counter electromotive force due to the motor inductance. Determine the value of overcurrent for the steady state, taking the peak current for reversing or applying a brake to the motor into consideration.

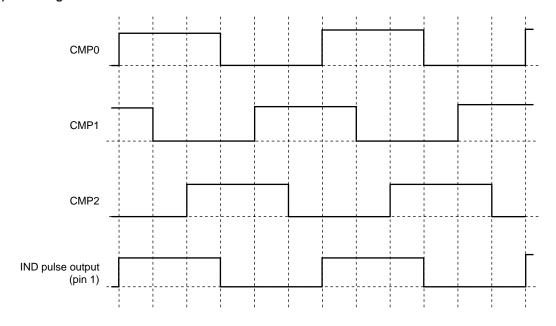


TIMING CHARTS

(1) Hole signal input



(2) CMP signal



(3) Output MOS FET driving and comparator selection (blank: switch OFF)

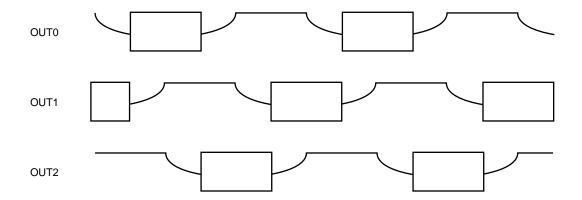
Q1		(SW)	(SW)		ON	ON		(SW)	(SW)		ON	ON	
Q2		SW	SW					SW	SW				
Q3	(SW)		ON	ON		(SW)	(SW)		ON	ON		(\overline{SW})	(SW)
Q4	SW					SW	SW					SW	SW
Q5	ON	ON		(SW)	(SW)		ON	ON		(SW)	(SW)		ON
Q6				SW	SW					SW	SW		

The high-side MOS FET at the output stage of the μ PD16858C performs synchronous switching (switching in parentheses).

The high-side MOS FET of the μ PD16858B does not perform switching in parentheses but is in the OFF state.



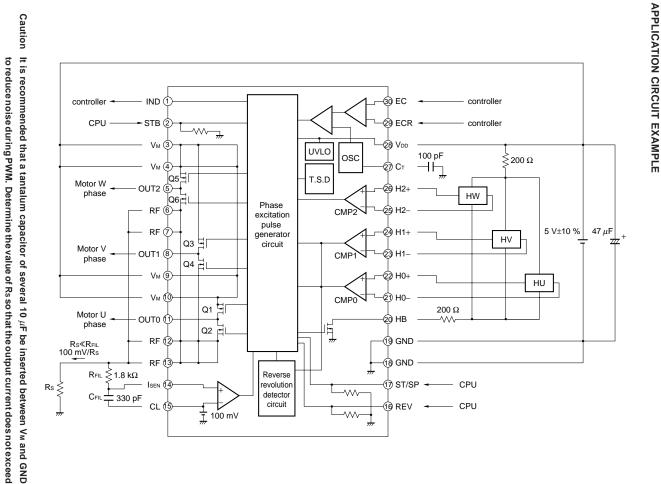
(4) Motor driving wave



Data Sheet S13480EJ3V0DS00

the rating.

Phase-out/Discontinued

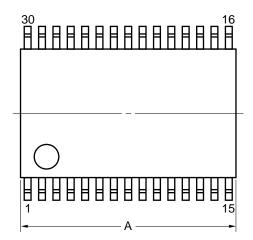




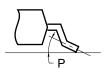


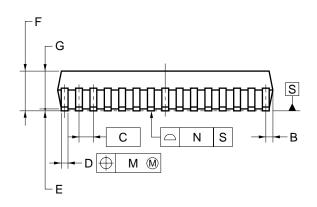
PACKAGE DRAWING

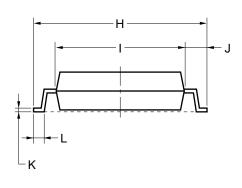
30 PIN PLASTIC SHRINK SOP (300 mil)



detail of lead end







NOTES

- 1. Controlling dimension millimeter.
- 2. Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	9.85±0.26	0.388±0.011
В	0.51 MAX.	0.020 MAX.
С	0.65 (T.P.)	0.026 (T.P.)
D	$0.32^{+0.08}_{-0.07}$	$0.013^{+0.003}_{-0.004}$
E	0.125±0.075	0.005±0.003
F	2.0 MAX.	0.079 MAX.
G	1.7±0.1	0.067±0.004
Н	8.1±0.2	0.319±0.008
I	6.1±0.2	0.240±0.008
J	1.0±0.2	$0.039^{+0.009}_{-0.008}$
K	$0.17^{+0.08}_{-0.07}$	$0.007^{+0.003}_{-0.004}$
L	0.5±0.2	0.020+0.008
М	0.10	0.004
N	0.10	0.004
Р	3°+7°	3°+7°

P30GS-65-300B-2



RECOMMENDED SOLDERING CONDITONS

Solder this product under the following recommended conditions.

For details of the recommended soldering conditions, refer to information document **Semiconductor Device Mounting Technology Manual (C10535E)**.

For soldering methods and conditions other than those recommended, consult NEC.

Soldering Method(s)	Soldering Conditions	Recommended Conditions Symbol
Infrared reflow	Package peak temperature: 235 °C, Time: 30 sec max. (210 °C min.), Number of times: three times max., Number of days: None ^{Note} , Flux: Rosin-based flux with little chlorine content (chlorine: 0.2 Wt% max.) is recommended.	IR35-00-3
VPS	Package peak temperature: 215 °C, Time: 40 sec max. (200 °C min.), Number of times: three times max., Number of days: None ^{Note} , Flux: Rosin-based flux with little chlorine content (chlorine: 0.2 Wt% max.) is recommended.	VP15-00-3
Wave soldering	Package peak temperature: 260 °C, Time: 10 sec max., Preheating temperature: 120 °C max., Number of times: once, Flux: Rosin-based flux with little chlorine content (chlorine: 0.2 Wt% max.) is recommended.	WS60-00-1

Note Number of days in storage after the dry pack has been opened. The storage conditions are at 25 °C, 65% RH MAX.

Caution Do not use two or more soldering methods in combination.

[MEMO]

[MEMO]



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